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Sheet 1 of 1

Complete if Known

Application Number 10/681,108-Conf. #8110
 Filing Date October 9, 2003
 First Named Inventor Chandra Mouli
 Art Unit 2811 ~~2829~~ 2891
 Examiner Name Not Yet Assigned
 Attorney Docket Number M4065.0762/P762

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
LT	AA	P. BOULON et al., "Anomalous Short Channel Effects in Indium Implanted nMOSFETS," 1997 IEEE.	
LT	AB	Y. LEE et al., "Indium Doped nMOSFETs and Buried Channel pMOSFETs with n+ Polysilicon Gate," Jpn. J. Appl. Phys. Vol. 36 (1997), pp. 1341-1345.	
LT	AC	I. C. KIZILYALLI et al., "n+ Polysilicon Gate PMOSFET's with Indium Doped Buried-Channels," IEEE Electron Device Letters, Vol. 17 (1996), pp. 46-49.	
LT	AD	G. G. SHAHIDI, "Indium Channel Implants for Improved MOSFET Behavior at the 100-nm Channel Length Regime," IEEE Transactions on Electronic Devices, Vol. 36 (1989) p. 2605.	
LT	AE	H. TIAN et al., "A Comparative Study of Indium and Boron Implanted Silicon Bipolar Transistors," IEEE Transactions on Electron Devices, Vol. 48 (2001), pp.2520-2524	

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Luan Thai

3/14/05